Electronic Supplementary Information

Chemically exfoliated transition metal dichalcogenide nanosheets-based wearable thermoelectric generators

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Fig. S1. TEM images of chemically exfoliated WS_2 and $NbSe_2$ nanosheets.



Fig. S2. Film thickness and morphology for vacuum-filtrated and transferred TMDC films on a 300nm-thick SiO_2/Si substrate. SEM images showing cross-section of a) WS_2 and b) $NbSe_2$ films and the film morphology of c) WS_2 and d) $NbSe_2$ films.



Fig. S3. XPS spectra for chalcogenides in chemically exfoliated a) WS_2 and b) $NbSe_2$.



Fig. S4. The long-term stability of a single unit under the thermal stress ($\Delta 60 \text{ K}$).